# RENESAS FemtoClock® Crystal-to-HSTL Frequency Synthesizer

DATA SHEET

# GENERAL DESCRIPTION

The 8421002I-01 is a 2 output HSTL Synthesizer optimized to generate Ethernet reference clock frequencies and is a member of the HiPerClocks<sup>™</sup> family of high performance clock solutions from IDT. Using a 25MHz, 18pF parallel resonant crystal, the following frequencies can be generated based on the 2 frequency select pins (F\_SEL[1:0]): 156.25MHz, 125MHz and 62.5MHz. The 8421002I-01 uses IDT's 3rd generation low phase noise VCO technology and can achieve 1ps or lower typical rms phase litter, easily meeting Ethernet jitter requirements. The 8421002I-01 is packaged in a small 20-pin TSSOP package.

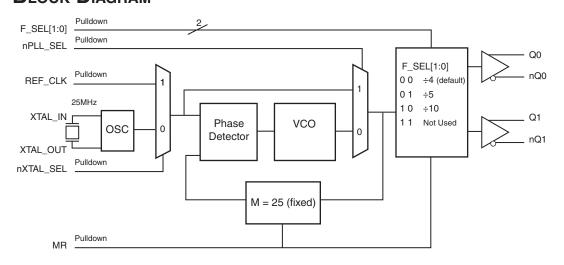
# **F**EATURES

- Two HSTL outputs (VOHmax = 1.5V)
- Selectable crystal oscillator interface or LVCMOS/LVTTL single-ended input
- Supports the following output frequencies: 156.25MHz, 125MHz, 62.5MHz
- VCO range: 560MHz 680MHz
- RMS phase jitter @ 156.25MHz, using a 25MHz crystal (1.875MHz - 20MHz): 0.44ps (typical)
- · Power supply modes: Core/Output 3.3V/1.8V 2.5V/1.8V
- -40°C to 85°C ambient operating temperature
- Available in lead-free (RoHS 6) compliant package

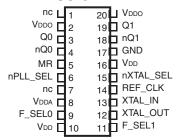
#### FREQUENCY SELECT FUNCTION TABLE

				Output Frequency
F_SEL1	F_SEL0	M Divider Value	M Divider   N Divider   (25M	
0	0	25	4	156.25
0	1	25	5	125
1	0	25	10	62.5
1	1	not u	ısed	not used

# **BLOCK DIAGRAM**



# PIN ASSIGNMENT



### 8421002I-01 20-Lead TSSOP

6.5mm x 4.4mm x 0.92mm package body **G** Package

Top View



TABLE 1. PIN DESCRIPTIONS

Number	Name	Ty	/ре	Description
1, 7	nc	Unused		No connect.
2, 20	V <sub>DDO</sub>	Power		Output supply pins.
3, 4	Q0, nQ0	Ouput		Differential output pair. HSTL interface levels.
5	MR	Input	Pulldown	Active HIGH Master Reset. When logic HIGH, the internal dividers are reset causing the true outputs Qx to go low and the inverted outputs nQx to go high. When logic LOW, the internal dividers and the outputs are enabled. LVCMOS/LVTTL interface levels.
6	nPLL_SEL	Input	Pulldown	Selects between the PLL and REF_CLK as input to the dividers. When LOW, selects PLL (PLL Enable). When HIGH, deselects the reference clock (PLL Bypass). LVCMOS/LVTTL interface levels.
8	V <sub>DDA</sub>	Power		Analog supply pin.
9, 11	F_SEL0, F_SEL1	Input	Pulldown	Frequency select pins. LVCMOS/LVTTL interface levels.
10, 16	V <sub>DD</sub>	Power		Core supply pin.
12, 13	XTAL_OUT, XTAL_IN	Input		Parallel resonant crystal interface. XTAL_OUT is the output, XTAL_IN is the input.
14	REF_CLK	Input	Pulldown	LVCMOS/LVTTL reference clock input.
15	nXTAL_SEL	Input	Pulldown	Selects between crystal or REF_CLK inputs as the the PLL Reference source. Selects XTAL inputs when LOW. Selects REF_CLK when HIGH. LVCMOS/LVTTL interface levels.
17	GND	Power		Power supply ground.
18, 19	nQ1, Q1	Output		Differential output pair. HSTL interface levels.

NOTE: Pulldown refers to internal input resistors. See Table 2, Pin Characteristics, for typical values.

Table 2. Pin Characteristics

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C	Input Capacitance			4		pF
R	Input Pulldown Resistor			51		kΩ



#### ABSOLUTE MAXIMUM RATINGS

Supply Voltage, V<sub>nn</sub> 4.6V

Inputs,  $V_{po}$  -0.5V to  $V_{po}$  + 0.5V

Outputs, I

Continuous Current 50mA Surge Current 100mA

Package Thermal Impedance,  $\theta_{_{\rm JA}}$  73.2°C/W (0 lfpm) Storage Temperature, T $_{_{\rm STG}}$  -65°C to 150°C

NOTE: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Table 3A. Power Supply DC Characteristics,  $V_{DD} = V_{DDA} = 3.3V \pm 5\%$ ,  $V_{DDO} = 1.8V \pm 0.2V$ , Ta = -40°C to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V <sub>DD</sub>	Core Supply Voltage		3.135	3.3	3.465	V
V <sub>DDA</sub>	Analog Supply Voltage		3.135	3.3	3.465	V
V	Output Supply Voltage		1.6	1.8	2.0	V
l <sub>DD</sub>	Power Supply Current				110	mA
I <sub>DDA</sub>	Analog Supply Current				12	mA
I <sub>DDO</sub>	Output Supply Current	No Load		0		mA

Table 3B. Power Supply DC Characteristics,  $V_{DD} = V_{DDA} = 2.5V \pm 5\%$ ,  $V_{DDO} = 1.8V \pm 0.2V$ , Ta = -40°C to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V <sub>DD</sub>	Core Supply Voltage		2.375	2.5	2.625	V
V	Analog Supply Voltage		2.375	2.5	2.625	V
V	Output Supply Voltage		1.6	1.8	2.0	V
I <sub>DD</sub>	Power Supply Current				96	mA
DDA	Analog Supply Current				12	mA
I <sub>DDO</sub>	Output Supply Current	No Load		0		mA

 $\textbf{TABLE 3C. LVCMOS / LVTTL DC Characteristics, V}_{\text{DD}} = V_{\text{DDA}} = 3.3 \text{V} \pm 5\% \text{ or } 2.5 \text{V} \pm 5\%, V_{\text{DDO}} = 1.8 \text{V} \pm 0.2 \text{V}, \text{TA} = -40 ^{\circ}\text{C} \text{ to } 85 ^{\circ}\text{C}$ 

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
V	Input High Vol	tana	V <sub>DD</sub> = 3.3V	2		V <sub>DD</sub> + 0.3	V
V <sub>IH</sub>	Imput riigir voi	lage	$V_{_{\rm DD}} = 2.5 V$	1.7		V <sub>DD</sub> + 0.3	V
V	Input		$V_{_{DD}} = 3.3V$	-0.3		0.8	V
V <sub>IL</sub>	Low Voltage		$V_{_{DD}} = 2.5V$	-0.3		0.7	V
I <sub>IH</sub>	Input High Current	REF_CLK, MR, F_SEL0, F_SEL1, nPLL_SEL, nXTAL_SEL	$V_{DD} = V_{IN} = 3.465V$ or 2.5V			150	μΑ
I <sub>IL</sub>	Input Low Current	REF_CLK, MR, F_SEL0, F_SEL1, nPLL_SEL, nXTAL_SEL	$V_{DD} = 3.465V \text{ or } 2.5V,$ $V_{IN} = 0V$	-150			μΑ



Table 3D. HSTL DC Characteristics,  $V_{_{DD}} = V_{_{DDA}} = 3.3V \pm 5\%$ ,  $V_{_{DDO}} = 1.8V \pm 0.2V$ , Ta = -40°C to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V <sub>OH</sub>	Output High Voltage; NOTE 1		1.0		1.5	V
V <sub>OL</sub>	Output Low Voltage; NOTE 1		0		0.5	V
V <sub>ox</sub>	Output Crossover Voltage; NOTE 2		40		60	%
V	Peak-to-Peak Output Voltage Swing		0.6		1.3	V

NOTE 1: Outputs terminated with  $50\Omega$  to ground.

NOTE 2: Defined with respect to output voltage swing at a given condition.

**Table 3E. HSTL DC Characteristics,**  $V_{_{DD}} = V_{_{DDA}} = 2.5V \pm 5\%$ ,  $V_{_{DDO}} = 1.8V \pm 0.2V$ , Ta = -40°C to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V <sub>OH</sub>	Output High Voltage; NOTE 1		0.8		1.5	V
V <sub>OL</sub>	Output Low Voltage; NOTE 1		0		0.6	V
V <sub>ox</sub>	Output Crossover Voltage; NOTE 2		40		60	%
V	Peak-to-Peak Output Voltage Swing		0.5		1.5	V

NOTE 1: Outputs terminated with  $50\Omega$  to ground.

NOTE 2: Defined with respect to output voltage swing at a given condition.

TABLE 4. CRYSTAL CHARACTERISTICS

Parameter	Test Conditions	Minimum	Typical	Maximum	Units
Mode of Oscillation		Fu	ındamenta	I	
Frequency		22.4	25	27.2	MHz
Equivalent Series Resistance (ESR)				50	Ω
Shunt Capacitance				7	pF
Drive Level				1	mW

NOTE: Characterized using an 18pF parallel resonant crystal.



**Table 5A. AC Characteristics,**  $V_{dd} = V_{dda} = 3.3V \pm 5\%, V_{ddo} = 1.8V \pm 0.2V,$  Ta = -40°C to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
		F_SEL[1:0] = 00	140		170	MHz
f <sub>OUT</sub>	Output Frequency	F_SEL[1:0] = 01	112		136	MHz
		F_SEL[1:0] = 10	56		68	MHz
tsk(o)	Output Skew; NOTE 1, 3				20	ps
	DMO DI L'II (D. I.)	156.25MHz, (1.875MHz - 20MHz)		0.44		ps
tjit(Ø)	RMS Phase Jitter (Random); NOTE 2	125MHz, (1.875MHz - 20MHz)		0.48		ps
	110122	62.5MHz,(1.875MHz - 20MHz)		0.49		ps
t <sub>r</sub> / t <sub>r</sub>	Output Rise/Fall Time	20% to 80%	215		815	ps
odc	Output Duty Cycle		48		52	%

NOTE 1: Defined as skew between outputs at the same supply voltages and with equal load conditions.

Measured at V<sub>DDO</sub>/2.

NOTE 2: Please refer to the Phase Noise Plot.

NOTE 3: This parameter is defined in accordance with JEDEC Standard 65.

**Table 5B. AC Characteristics,**  $V_{DD} = V_{DDA} = 2.5V \pm 5\%$ ,  $V_{DDO} = 1.8V \pm 0.2V$ , TA = -40°C to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
		F_SEL[1:0] = 00	140		170	MHz
f <sub>оит</sub>	Output Frequency	F_SEL[1:0] = 01	112		136	MHz
		F_SEL[1:0] = 10	56		68	MHz
tsk(o)	Output Skew; NOTE 1, 3				20	ps
		156.25MHz, (1.875MHz - 20MHz)		0.41		ps
tjit(Ø)	RMS Phase Jitter (Random); NOTE 2	125MHz, (1.875MHz - 20MHz)		0.49		ps
		62.5MHz,(1.875MHz - 20MHz)		0.50		ps
t <sub>R</sub> / t <sub>F</sub>	Output Rise/Fall Time	20% to 80%	315		715	ps
odc	Output Duty Cycle		48		52	%

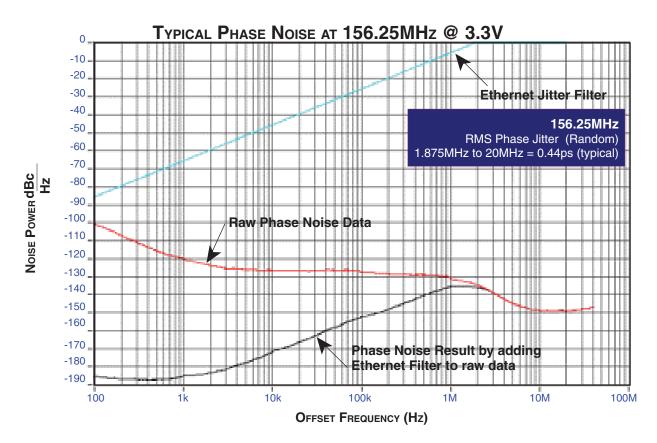
NOTE 1: Defined as skew between outputs at the same supply voltages and with equal load conditions.

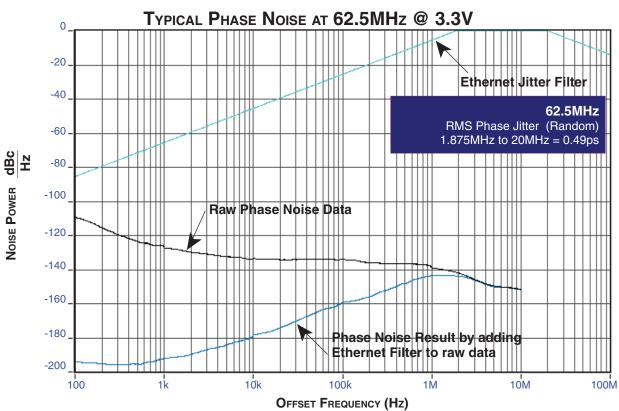
Measured at  $V_{DDO}/2$ .

NOTE 2 Please refer to the Phase Noise Plot.

NOTE 3 This parameter is defined in accordance with JEDEC Standard 65.

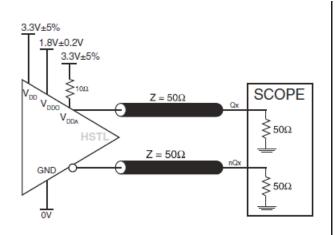


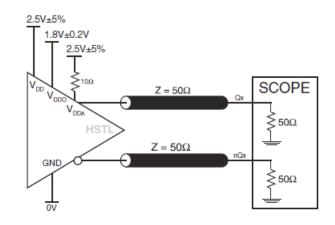






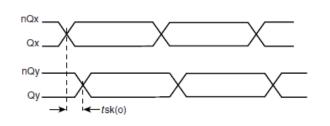
# PARAMETER MEASUREMENT INFORMATION

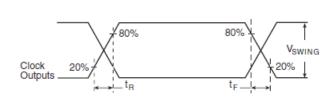




# HSTL 3.3V/1.8V OUTPUT LOAD AC TEST CIRCUIT

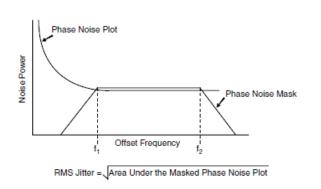


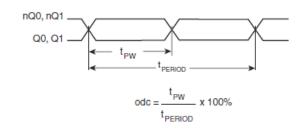




# **OUTPUT SKEW**

# OUTPUT RISE/FALL TIME





**RMS PHASE JITTER** 

OUTPUT DUTY CYCLE/PULSE WIDTH/PERIOD



# **APPLICATION INFORMATION**

### Power Supply Filtering Techniques

As in any high speed analog circuitry, the power supply pins are vulnerable to random noise. The 8421002I-01 provides separate power supplies to isolate any high switching noise from the outputs to the internal PLL.  $V_{\text{DD}},\,V_{\text{DDA}},\,$  and  $V_{\text{DDD}}$  should be individually connected to the power supply plane through vias, and bypass capacitors should be used for each pin. To achieve optimum jitter performance, power supply isolation is required. Figure 1 illustrates how a  $10\Omega$  resistor along with a  $10\mu\text{F}$  and a  $.01\mu\text{F}$  bypass capacitor should be connected to each  $V_{\text{DDA}}$ .

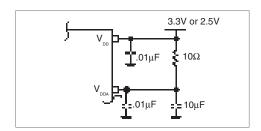


FIGURE 1. POWER SUPPLY FILTERING

### **CRYSTAL INPUT INTERFACE**

The 8421002I-01 has been characterized with 18pF parallel resonant crystals. The capacitor values shown in *Figure 2* below

were determined using a 25MHz, 18pF parallel resonant crystal and were chosen to minimize the ppm error.

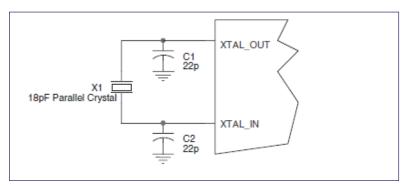


Figure 2. CRYSTAL INPUT INTERFACE

### RECOMMENDATIONS FOR UNUSED INPUT AND OUTPUT PINS

#### INPUTS:

#### CRYSTAL INPUT:

For applications not requiring the use of the crystal oscillator input, both XTAL\_IN and XTAL\_OUT can be left floating. Though not required, but for additional protection, a  $1 k\Omega$  resistor can be tied from XTAL\_IN to ground.

#### REF\_CLK INPUT:

For applications not requiring the use of the reference clock, it can be left floating. Though not required, but for additional protection, a  $1k\Omega$  resistor can be tied from the REF\_CLK to ground.

#### LVCMOS CONTROL PINS:

All control pins have internal pull-ups or pull-downs; additional resistance is not required but can be added for additional protection. A  $1k\Omega$  resistor can be used.

## **OUTPUTS:**

#### **HSTL O**UTPUT

All unused HSTL outputs can be left floating. We recommend that there is no trace attached. Both sides of the differential output pair should either be left floating or terminated.



# POWER CONSIDERATIONS

This section provides information on power dissipation and junction temperature for the 8421002I-01. Equations and example calculations are also provided.

#### 1. Power Dissipation.

The total power dissipation for the 8421002I-01 is the sum of the core power plus the power dissipated in the load(s). The following is the power dissipation for  $V_{nn} = 3.3V + 5\% = 3.465V$ , which gives worst case results.

NOTE: Please refer to Section 3 for details on calculating power dissipated in the load.

- Power (core)<sub>MAX</sub> = V<sub>DD\_MAX</sub> \* I<sub>DD\_MAX</sub> = 3.465V \* 122mA = 422.7mW
- Power (outputs)<sub>MAX</sub> = 32.8mW/Loaded Output pair
   If all outputs are loaded, the total power is 2 \* 32.8mW = 65.6mW

Total Power  $_{MAX}$  (3.465V, with all outputs switching) = 422.7mW + 65.6mW = 488.3mW

#### 2. Junction Temperature.

Junction temperature, Tj, is the temperature at the junction of the bond wire and bond pad and directly affects the reliability of the device. The maximum recommended junction temperature for HiPerClockS™ devices is 125°C.

The equation for Tj is as follows: Tj =  $\theta_{JA}$  \* Pd\_total + T<sub>A</sub>

Tj = Junction Temperature

 $\theta_{JA}$  = Junction-to-Ambient Thermal Resistance

Pd\_total = Total Device Power Dissipation (example calculation is in section 1 above)

T<sub>A</sub> = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance  $\theta_{JA}$  must be used. Assuming a moderate air flow of 200 linear feet per minute and a multi-layer board, the appropriate value is  $66.6^{\circ}$ C/W per Table 6 below.

Therefore, Tj for an ambient temperature of 85°C with all outputs switching is:  $85^{\circ}\text{C} + 0.488\text{W} * 66.6^{\circ}\text{C/W} = 117.5^{\circ}\text{C}$ . This is below the limit of 125°C.

This calculation is only an example. Tj will obviously vary depending on the number of loaded outputs, supply voltage, air flow, and the type of board (single layer or multi-layer).

Table 6. Thermal Resistance  $\theta_{JA}$  for 20-pin TSSOP, Forced Convection

# θ<sub>JA</sub> by Velocity (Linear Feet per Minute)

0200500Single-Layer PCB, JEDEC Standard Test Boards114.5°C/W98.0°C/W88.0°C/WMulti-Layer PCB, JEDEC Standard Test Boards73.2°C/W66.6°C/W63.5°C/W

NOTE: Most modern PCB designs use multi-layered boards. The data in the second row pertains to most designs.



## 3. Calculations and Equations.

The purpose of this section is to derive the power dissipated into the load.

HSTL output driver circuit and termination are shown in Figure 3.

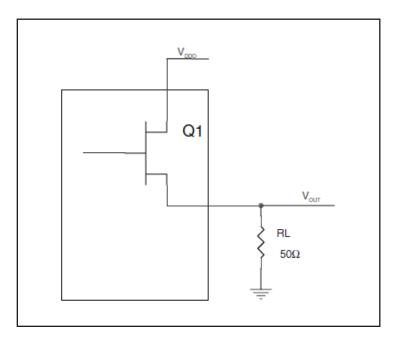


FIGURE 3. HSTL DRIVER CIRCUIT AND TERMINATION

To calculate worst case power dissipation into the load, use the following equations which assume a  $50\Omega$  load.

Pd\_H is power dissipation when the output drives high.

Pd\_L is the power dissipation when the output drives low.

$$Pd\_H = (V_{OH\_MAX}/R_L) * (V_{DD\_MAX} - V_{OH\_MAX})$$

$$Pd\_L = (V_{OL\_MAX}/R_L) * (V_{DD\_MAX} - V_{OL\_MAX})$$

$$Pd_H = (1V/50\Omega) * (2V - 1V) = 20mW$$

$$Pd_L = (0.4V/50\Omega) * (2V - 0.4V) = 12.8mW$$

Total Power Dissipation per output pair =  $Pd_H + Pd_L = 32.8mW$ 



# **RELIABILITY INFORMATION**

Table 7.  $\theta_{_{JA}} \text{vs. Air Flow Table for 20 Lead TSSOP}$ 

# θ<sub>JA</sub> by Velocity (Linear Feet per Minute)

0200500Single-Layer PCB, JEDEC Standard Test Boards114.5°C/W98.0°C/W88.0°C/WMulti-Layer PCB, JEDEC Standard Test Boards73.2°C/W66.6°C/W63.5°C/W

NOTE: Most modern PCB designs use multi-layered boards. The data in the second row pertains to most designs.

### **TRANSISTOR COUNT**

The transistor count for 8421002I-01 is: 2951



# PACKAGE OUTLINE - G SUFFIX FOR 20 LEAD TSSOP

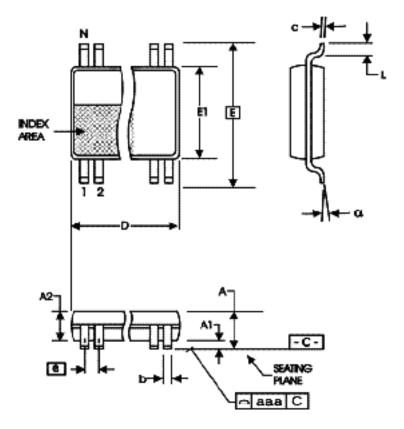


TABLE 8. PACKAGE DIMENSIONS

SYMBOL	Millin	neters
STWIDGE	MIN	MAX
N	2	0
А		1.20
A1	0.05	0.15
A2	0.80	1.05
b	0.19	0.30
С	0.09	0.20
D	6.40	6.60
E	6.40 E	BASIC
E1	4.30	4.50
е	0.65 E	BASIC
L	0.45	0.75
α	0°	8°
aaa		0.10

Reference Document: JEDEC Publication 95, MO-153



# Table 9. Ordering Information

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
ICS8421002AGI-01LF	ICS1002AI01L	20 Lead "Lead-Free" TSSOP	tube	-40°C to 85°C
ICS8421002AGI-01LFT	ICS1002AI01L	20 Lead "Lead-Free" TSSOP	tape & reel	-40°C to 85°C

NOTE: Parts that are ordered with an "LF" suffix to the part number are the Pb-Free Configuration and are RoHS compliant.



REVISION HISTORY SHEET					
Rev	Table	Page	Description of Change		
В	3A, 3B	3	Power Supply Tables - corrected V <sub>DDD</sub> min/max.	8/8/06	
В	T9	13	Ordering Information - removed leaded devices. Updated data sheet format.	4/6/15	
В			Product Discontinuation Notice - Last time buy expires August 14, 2016 PDN CQ-15-04	8/14/15	



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